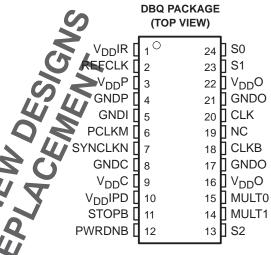
- 533-MHz Differential Clock Source for Direct Rambus[™] Memory Systems for an 1066-MHz Data Transfer Rate
- Synchronizes the Clock Domains of the Rambus Channel With an External System or Processor Clock
- Three Power Operating Modes to Minimize Power for Mobile and Other Power-Sensitive Applications
- Operates From a Single 3.3-V Supply and 120 mW at 300 MHz (Typ)
- Packaged in a Shrink Small-Outline Package (DBQ)
- Supports Frequency Multipliers: 4, 6, 8, 16/3
- No External Components Required for PLL
- Supports Independent Channel Clocking
- Spread Spectrum Clocking Tracking Capability to Reduce EMI
- Designed for Use With TI's 133-MHz Clock Synthesizers CDC924 and CDC921

- Cycle-Cycle Jitter Is Less Than 40 ps at 533 MHz
- Certified by Gigatest Labs to Exceed the Rambus DRCG Validation Requirement
- Supports Industrial Temperature Range of -40°C to 85°C



NC - No internal connection

description

The Direct Rambus clock generator (DRCG) provides the necessary clock signals to support a Direct Rambus memory subsystem. It includes signals to synchronize the Direct Rambus channel clock to an external system or processor clock. It is designed to support Direct Rambus memory on a desktop, workstation, server, and mobile PC motherboards. DRCG also provides an off-the-shelf solution for a broad range of Direct Rambus memory applications.

The DRCG provides clock multiplication and phase alignment for a Direct Rambus memory subsystem to enable synchronous communication between the Rambus channel and ASIC clock domains. In a Direct Rambus memory subsystem, a system clock source provides the REFCLK and PCLK clock references to the DRCG and memory controller, respectively. The DRCG multiplies REFCLK and drives a high-speed BUSCLK to RDRAMs and the memory controller. Gear ratio logic in the memory controller divides the PCLK and BUSCLK frequencies by ratios M and N such that PCLKM = SYNCLKN, where SYNCLK = BUSCLK/4. The DRCG detects the phase difference between PCLKM and SYNCLKN and adjusts the phase of BUSCLK such that the skew between PCLKM and SYNCLKN is minimized. This allows data to be transferred across the SYNCLK/PCLK boundary without incurring additional latency.

User control is provided by multiply and mode selection terminals. The multiply terminals provide selection of one of four clock frequency multiply ratios, generating BUSCLK frequencies ranging from 267 MHz to 533 MHz with clock references ranging from 33 MHz to 100 MHz. The mode select terminals can be used to select a bypass mode where the frequency multiplied reference clock is directly output to the Rambus channel for systems where syncuronization between the Rambus clock and a system clock is not required. Test modes are provided to bypass the PLL and output REFCLK on the Rambus channel and to place the outputs in a high-impedance state for board testing.

The CDCFR83 is characterized for operation over free-air temperatures of -40°C to 85°C.

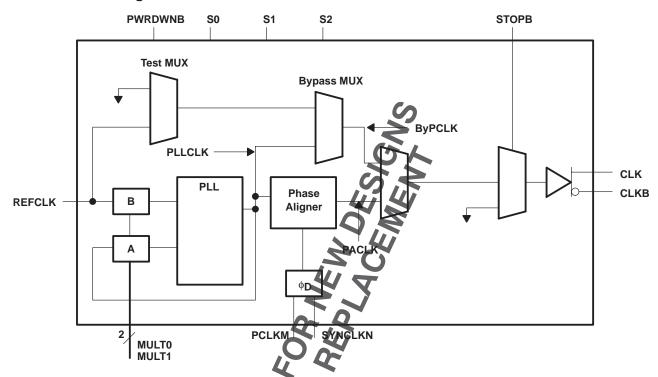


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Direct Rambus and Rambus are trademarks of Rambus Inc.

TEXAS INSTRUMENTS

functional block diagram



FUN	CTION	TABL	ΕŤ
4 014	Official	IADL	ъ.

			1 0.11	TON MELL.	
MODE S0 \$		31	S2	CLK	CLKB
Normal	0	9	9	Phase aligned clock	Phase aligned clock B
Bypass	1	7/	Ó	PLLCLK	PLLCLKB
Test	1	V	9	REFCLK	REFCLKB
Output test (OE)	ø	Ċ	X	Hi-Z	Hi-Z
Reserved	9	8	1		
Reserved		0	1	_	_
Reserved	71	1	1	Hi-Z	Hi-Z

†X = don't care, Hi Z = high impedance



Terminal Functions

NAME NO. VO DESCRIPTION CLK 20 0 Output clock (complement) GNDC 3 0 Output clock (complement) GNDI 5 1 GND for phase aligner GNDI 5 1 GND for clock outputs GNDP 4 0 SND for LL MULT0 15 1 PLL multiplier select MULT1 14 1 PLL multiplier select MULT1 14 1 PL multiplier select MUCT 19 1 Not used PCLKM 6 1 Phase detector input PCLKM 6 1 Phase detector input PWRDNB 12 1 Active low power down REFCLK 2 1 Reference clock S0 24 1 Mode control S1 23 1 Active low output disable SYNCLKN 7 1 Phase detector input VpDif 1 <t< th=""><th>TERMIN</th><th>NAL</th><th>.,-</th><th></th></t<>	TERMIN	NAL	.,-	
CLKB	NAME	NO.	1/0	DESCRIPTION
GNDC	CLK	20	0	Output clock
GNDI	CLKB	18	0	Output clock (complement)
GNDO	GNDC	8		GND for phase aligner
GNDP	GNDI	5		GND for control inputs
MULTO 15 I PLL multiplier select MULT1 14 I PLL multiplier select NC 19 Not used PCLKM 6 I Phase detector input PWRDNB 12 I Active low power down REFCLK 2 I Reference clock S0 24 I Mode control S1 23 I Mode control S2 13 I Mode control STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDR 1 Reference voltage for REFCLK VDD 16,22 VDD for clock output VDD 16,22 VDD for clock output VDD 16,22 VDD for Clock output	GNDO	17, 21		GND for clock outputs
MULT1 14 I PLL multiplier select NC 19 Not used PCLKM 6 I Phase detector input PWRDNB 12 I Active low power down REFCLK 2 I Reference clock S0 24 I Mode control S1 23 I Mode control S2 13 I Mode control STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 Vpp for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for RBFCLK VpD 3 Vpp for PLL	GNDP	4		GND for PLL
NC 19 Not used PCLKM 6 I Phase detector input PWRDNB 12 I Active low power down REFCLK 2 I Reference clock S0 24 I Mode control S1 23 I Mode control S2 13 I Mode control STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for RB-CLK VDDO 16,22 VDD for clock outplut VDDP 3 VDD for PLL	MULT0	15	I	PLL multiplier select
PCLKM 6 I Phase detector input PWRDNB 12 I Active low power down REFCLK 2 I Reference clock S0 24 I Mode control S1 23 I Mode control S2 13 I Mode control STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for RBFCLK VDDO 16, 22 VDD for clock output VDDP 3 VDD for PLL	MULT1	14	I	PLL multiplier select
PWRDNB 12 I Active low power down REFCLK 2 I Reference clock S0 24 I Mode control S1 23 I Mode control S2 13 I Mode control STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for REFCLK VDDO 16, 22 VDD for clock output VDDP 3 VDD for PLL	NC	19		Not used
REFCLK 2 I Reference clock S0 24 I Mode control S1 23 I Mode control S2 13 I Mode control STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 VDp for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for REFCLK VDDO 16, 22 VDp for clock outputs VDDP 3 VDp for PLL	PCLKM	6	ı	Phase detector input
S0	PWRDNB	12	I	Active low power down
S1 23 I Mode control S2 13 I Mode control STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for REFCLK VDDO 16, 22 VDD for clock outputs VDDP 3 VDD for PLL	REFCLK	2	I	Reference clock
STOPB	S0	24	I	Mode control
STOPB 11 I Active low output disable SYNCLKN 7 I Phase detector input VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for REFCLK VDDO 16, 22 VDD for clock outputs VDDP 3 VDD for PLL	S1	23	I	Mode control
SYNCLKN 7 I Phase detector input VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for RFFCLK VDDO 16, 22 VDD for clock outputs VDDP 3 VDD for PLL	S2	13	I	Mode control
VDDC 9 VDD for phase aligner VDDIPD 10 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for RBFCLK VDDO 16, 22 VDD for clock outputs VDDP 3 VDD for PLL	STOPB	11	I	Active low output disable
VDDIR 1 Reference voltage for phase detector inputs and STOPB VDDIR 1 Reference voltage for REFCLK VDDO 16, 22 VDD for clock outputs VDDP 3 VDD for PLL	SYNCLKN	7	I	Phase detector input
VDDIR 1 Reference voltage for REFCLK VDDO 16, 22 VDD for clock outplut VDDP 3 VDD for PLL	$V_{DD}C$	9		V _{DD} for phase aligner
VDDO 16, 22 VDD for clock outputs VDDP 3 VDD for PLL	$V_{DD}IPD$	10		
V _{DD} P 3 V _{DD} for PLL	$V_{DD}IR$	1		Reference voltage for REFCLK
	$V_{DD}O$	16, 22		V _{DD} for clock outputs
SA SECOMMEN	$V_{DD}P$	3		V _{DD} for PLL
			<i>(</i>	SE COMME



PLL divider selection

Table 1 lists the supported REFCLK and BUSCLK frequencies. Other REFCLK frequencies are permitted, provided that (267 MHz < BUSCLK < 533 MHz) and (33 MHz < REFCLK < 100 MHz).

Table 1. REFCLK and BUSCLK Frequencies

MULT0	MULT1	REFCLK (MHz)	MULTIPLY RATIO	BUSCLK (MHz)
0	0	67	4	267
0	1	50	6	300
0	1	67	٥	400
1	1	33	V	267
1	1	50	8	400
1	1	67	8	533
1	0	67	16/3	356

Table 2. Clock Output Driver States

STATE	PWRDNB	STOPB 🙎	CLK	CLKB
Powerdown	0	Х	GND	GND
CLK stop	1	0	VX, STOP	V _X , STOP
Normal	1	1,0	PACLK/PLLCLK/ REFCLK†	PACLKB/PLLCLKB/ REFCLKB

[†] Depending on the state of S0, S1, and S2

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage range, V _{DD} (see Note1)	$-0.5\ V$ to 4 V
Output voltage range, V _O , at any output terminal	V _{DD} + 0.5 V
Input voltage range,V _I , at any input terminal	V _{DD} + 0.5 V
Continuous total power dissipation see Dissipation	Rating Table
Operating free-air temperature range. To	-40°C to 85°C
Storage temperature range, Tst	55°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. implied. Exposure to absolute-maximum-rate

DISSIPATION RATING TABLE

PACKAGE	TA ≥25°C	DERATING FACTOR	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C [‡]	POWER RATING	POWER RATING
DBQ	1400 mW	11 mW/°C	905 mW	740 mW

[‡]This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.



NOTE 1: All voltage values are with to the GND terminals.

recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V _{DD}	3.135	3.3	3.465	V
High-level input voltage, V _{IH} (CMOS)	$0.7 \times V_{DD}$			V
Low-level input voltage, V _{IL} (CMOS)			$0.3 \times V_{DD}$	V
Initial phase error at phase detector inputs (required range for phase aligner)	$-0.5 \times t_{C(PD)}$		$0.5 \times t_{C(PD)}$	
REFCLK low-level input voltage, V _{IL}	7		$0.3 \times V_{DD}IR$	V
REFCLK high-level input voltage, VIH	$0.7 \times V_{DD}IR$			V
Input signal low voltage, V _{IL} (STOPB)			$0.3 \times V_{DD}IPD$	V
Input signal high voltage, V _{IH} (STOPB)	$9.7 \times V_{DD}IPD$			V
Input reference voltage for (REFCLK) (VDDIR)	1.235		3.465	V
Input reference voltage for (PCLKM and SYSCLKN) (VDDIPD)	1.235		3.465	V
High-level output current, IOH	3		-16	mA
Low-level output current, IOL	7		16	mA
Operating free-air temperature, T _A	-40		85	°C

timing requirements

	MIN	MAX	UNIT
Input cycle time, t _{C(in)}	10	40	ns
Input cycle-to-cycle jitter		250	ps
Input duty cycle over 10,000 cycles	40%	60%	
Input frequency modulation, f _{mod}	30	33	kHz
Modulation index, nonlinear maximum 0.5%		0.6%	
Phase detector input cycle time (PCLKM and SYNCLKN)	30	100	ns
Input slew rate, SR	1	4	V/ns
Input duty cycle (PCLKM and SYNCLKN)	25%	75%	
107 A 60 C C C C C C C C C C C C C C C C C C			



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETE	R	TEST COI	NDITIONS†	MIN	TYP‡	MAX	UNIT
V _{O(STOP)}	Output voltage (STOPB = 0)	e during CLK Stop	See Figure 1		1.1		2	
$V_{O(X)}$	Output crossi	ng-point voltage	See Figure 1 and F	igure 6	1.3		1.8	V
Vo	Output voltage	e swing	See Figure 1	(0	0.4		0.6	V
V _{IK}	Input clamp v	oltage	$V_{DD} = 3.135 \text{ V},$	I _I = 18 mA			-1.2	V
			See Figure 1	<u> </u>			2	
VOH	High-level out	put voltage	V_{DD} = min to max,	IDH = -1 mA	V _{DD} – 0.1 V			V
			V _{DD} = 3.135 V,	OH = 16-mA	2.4			Ī
			See Figure 1	7. 41	1			·
VOL	Low-level out	out voltage	$V_{DD} = min to max$	I _{OL} = 1 mA			0.1	V
			$V_{DD} = 3.135 \text{ V},$	lol = 16 mA			0.5	Ī
			V _{DD} = 3.135 V	Vo ≠ 1 V	-32	-52		·
lOH	High-level out	put current	$V_{DD} = 3.3 V$	= 1.65 V		-51		mA
			$V_{DD} = 3.465 V$,	V _O = 3.135 V		-14.5	-21	Ī
			$V_{DD} = 3.135 \text{ V},$	V _O = 1.95 V	43	61.5		·
lOL	Low-level out	out current	V _{DD} ₹3 , V, Q	V _O = 1.65 V		65		mA
			V _{DD} = 3.465 V,	$V_0 = 0.4 V$		25.5	36	Ī
I _{OZ}	High-impedance-state output current		S 0 = 0, S1 = 1				±10	μΑ
I _{OZ(STOP)}	High-impedance-state output current during CLK stop		Stop = $0, V_O = GND \text{ or } V_{DD}$				±100	μΑ
I _{OZ(PD)}		nce-state output ver-down state	$\begin{array}{c} PWRDNB = 0, \\ V_O = GND \text{ or } V_{DD} \end{array}$		-10		100	μΑ
	High-level	REFCLK, PCLKM, SYNCLKN, STOPE	V _{DD} = 3.465 V,	$V_I = V_{DD}$			10	A
Iн	input current	PWRDNB, S0, S1, S2, MULT0, MULT1	$V_{DD} = 3.465 \text{ V},$	$V_I = V_{DD}$			10	μА
1	Low-level	REFCLK, PCLKM SYNCLKN, STOPB	V _{DD} = 3.465 V,	V _I = 0			-10	
I _{IL}	input current	PWRD NB, S0, S1, S2, MULT0, MULT1	V _{DD} = 3.465 V,	V _I = 0			-10	μΑ
7 -	Output	High state	R _I at I _O –14.5 mA t	o –16.5 mA	15	35	50	0
ZO	impedance	Low state	R _I at I _O 14.5 mA to	16.5 mA	11	17	35	Ω
	Reference	V _{DD} IR, V _{DD} IPD	V 2 465 V	PWRDNB = 0			50	μΑ
	current	ADDIM' ADDILD	V _{DD} = 3.465 V	PWRDNB = 1			0.5	mA
Cl	Input capacita	ince	$V_I = V_{DD}$ or GND			2		рF
CO	Output capac	tance	$V_O = V_{DD}$ or GND			3		pF
I _{DD(PD)}	Supply curren	t in power-down state	REFCLK = 0 MHz t PWDNB = 0,	o 100 MHz, STOPB = 1			100	μΑ
IDD(CLKSTOP)	Supply curren	t in CLK stop state	BUSCLK configured	d for 533 MHz			45	mA
IDD(NORMAL)	Supply curren	t in normal state	BUSCLK = 533 MH				100	mA
= \: : = : : : : : : : : : : : : : : : :			 		+			

[†] V_{DD} refers to any of the following; V_{DD} , $V_{DD}IPD$, $V_{DD}IR$, $V_{DD}O$, $V_{DD}C$, and $V_{DD}P$ ‡ All typical values are at $V_{DD} = 3.3 \text{ V}$, $T_A = 25^{\circ}C$.



switching characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	l		TEST CONDITIONS	MIN	TYP† M	٩X	UNIT
t _{c(out)}	Clock output cycle time				1.87	3	75	ns
			267 MHz				80	
	-	Infinite and	300 MHz				70	
t(jitter)	Total cycle jitter over 1, 2, 3, 4, 5, or 6 clock cycles	stopped phase	356 MHz	See Figure 3			60	ps
	o, 4, o, or o clock cycles	alignment	400 MHz	S			50	
			533 MHz§				40	
t(phase)	Phase detector phase error for distributed loop			Static phase error [‡]	-100	1	00	ps
t(phase, SSC)	PLL output phase error when tracking SSC			Dynamic phase error [‡]	-100	1	00	ps
t(DC)	Output duty cycle over 10,0	000 cycles	4	See Figure 4	45%	5	5%	
			267 MHz	12			80	
	Infinite	Infinite and	and 300 MHz				70	
t(DC, err)	Output cycle-to-cycle duty cycle error	stopped phase	356 MHz	See Figure 5			60	ps
	daty by old offici	alignment	400 MHz				50	
			533 MHz	V			50	
t _r , t _f	Output rise and fall times (measured at 20%–80% of output voltage)			See Figure 7	160	4	00	ps
Δt	Difference between rise an (20%–80%) t _f - t _r	d fall times on a	ingle device	See Figure 7		1	00	ps

[†] All typical values are at $V_{DD} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

state transition latency specification

	PARAMETER	FROM	то	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
	Delay time, PWRDNB↑ to CLK/SLKB output settled (excluding t(DISTLOSK))	D	No	See Figure 8			3	
^t (powerup)	Delay time, PWRDNB↑ to internal PLL and clock are on and settled	Powerdown	Normal				3	ms
	Delay time, power up to CLK/CLKB output settled	.,	N	See Figure 8			3	
t(VDDpowerup)	Delay time, power up to internal PLL and clock are on and settled	V _{DD}	Normal				3	ms
^t (MULT)	MULTO and MULT schange to CLK/CLKB output resettled (excluding (DISTLOCK))	Normal	Normal	See Figure 9			1	ms
t(CLKON)	STOPB↑ to CLK/CLKB gltch-free clock edges	CLK Stop	Normal	See Figure 10			10	ns
^t (CLKSETL)	STOPB to CLK/CLKB output settled to within 50 ps of the phase before STOPB was disabled	CLK Stop	Normal	See Figure 10			20	cycles
t(CLKOFF)	STOPB↓ to CLK/CLKB output disabled	Normal	CLK Stop	See Figure 10			5	ns

[†] All typical values are at $V_{DD} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



[‡] Assured by design § Jitter measurement according to Rambus validation specification

state transition latency specifications (continued)

	PARAMETER	FROM	то	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t(powerdown)	Delay time, PWRDNB↓ to the device in the power-down mode	Normal	Powerdown	See Figure 8			1	ms
t(STOP)	Maximum time in CLKSTOP (STOPB = 0) before reentering normal mode (STOPB = 1)	STOPB	Normal	See Figure 10			100	μs
t(ON)	Minimum time in normal mode (STOPB = 1) before reentering CLKSTOP (STOPB = 0)	Normal	CLK stop	See Figure 10	100			ms
t(DISTLOCK)	Time from when CLK/CLKB output is settled to when the phase error between SYNCLKN and PCLKM falls within t _(phase)	Unlocked	Locked				5	ms

 $[\]uparrow$ All typical values are at V_{DD} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

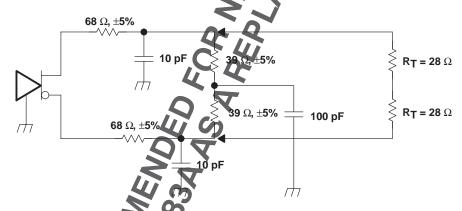


Figure 1. Test Load and Voltage Definitions $(V_{O(STOP)}, V_{O(X)}, V_O, V_{OH}, V_{OL})$

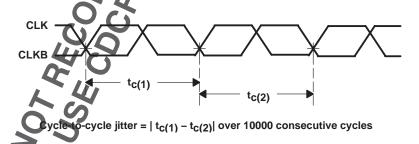
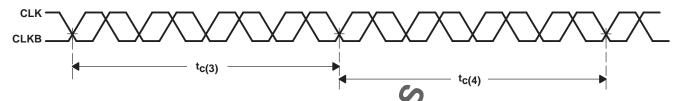


Figure 2. Cycle-to-Cycle Jitter

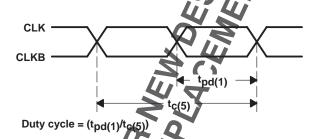


PARAMETER MEASUREMENT INFORMATION

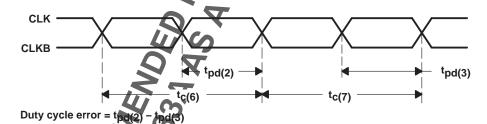


Cycle-to-cycle jitter = $|t_{C(3)} - t_{C(4)}|$ over 10000 consecutive cycles

Figure 3. Short Term Cycle-to-Cycle litter Over Four Cycles



utput Duty Cycle



uty Cycle Error (Cycle-to-Cycle)

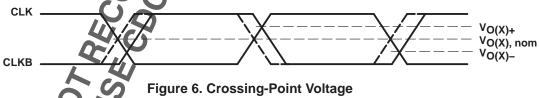
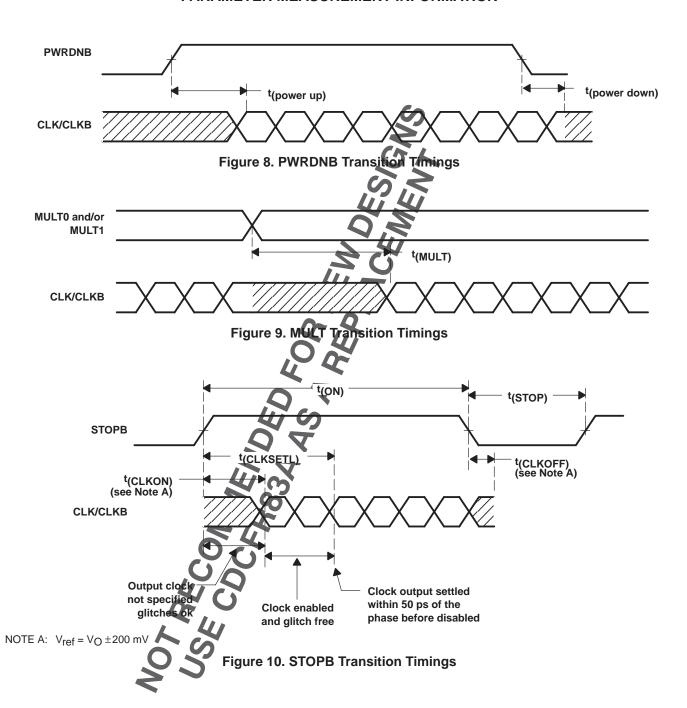




Figure 7. Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
CDCFR83DBQR	NRND	SSOP	DBQ	24	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CDCFR83	
CDCFR83DBQRG4	NRND	SSOP	DBQ	24	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CDCFR83	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

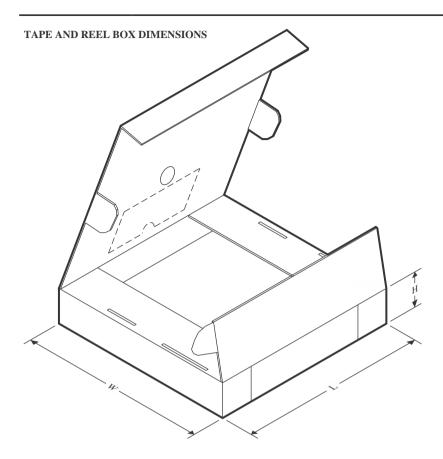


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCFR83DBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 3-Jun-2022



*All dimensions are nominal

Г	Device Package Ty		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
Г	CDCFR83DBQR	SSOP	DBQ	24	2500	356.0	356.0	35.0	

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